Lubrication Layer Perturbations in Chemical-Mechanical Polishing

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Outline

- A quick tutorial on chemical-mechanical polishing (CMP).

- Elastohydrodynamic lubrication with a pure lubricant.

- Questions posed by the presence of slurry particles.

Quick CMP Tutorial

Wafer Planarization in Integrated Circuit Fabrication

• Integrated circuits are made by deposition and modification of numerous material layers.
• Photolithography, the main method of creating patterns, works best on flat surfaces.
• Chemical-Mechanical Polishing (CMP) is currently the leading method for planarizing surfaces.
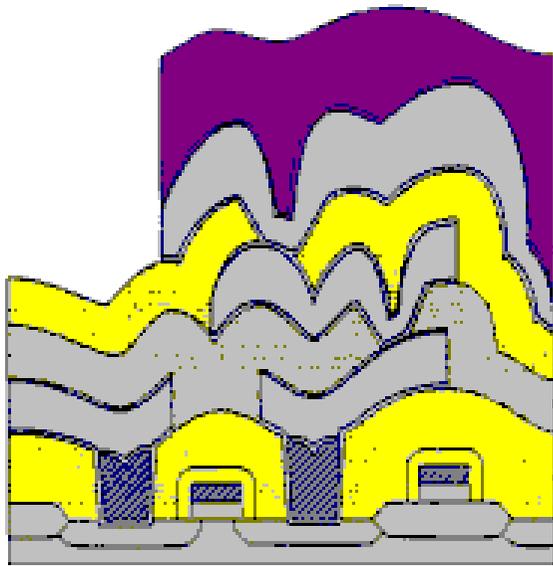
Peter Wolters

Schematic of an integrated circuit produced without CMP

Schematic of an integrated circuit produced with CMP

Generic Rotary Polishing Tool

A rotating tool with a diamond-covered face maintains pad surface roughness, counteracting abrasive wear, removing debris, exposing new pad surface.
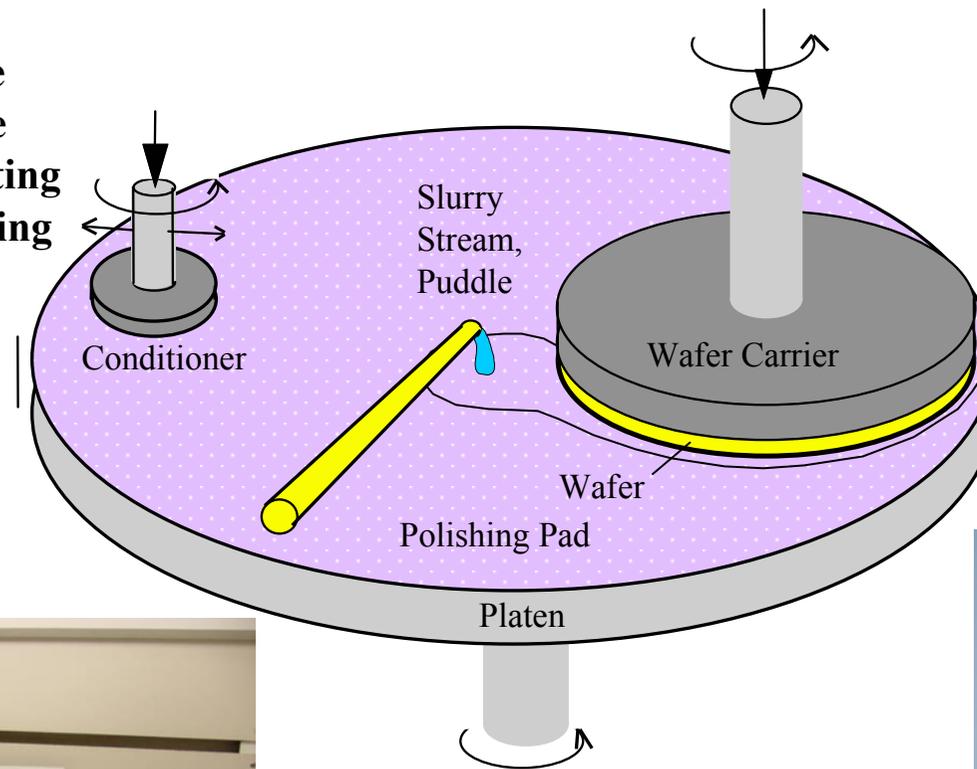
The wafer is held upside down by a rotating carrier. The wafer surface reacts with chemicals in the slurry and is abraded by slurry particles. The pad also experiences abrasive wear.

Slurry Stream, Puddle

Conditioner

Wafer Carrier

Wafer

Polishing Pad

Platen

Commercial tool
AMAT Reflexion
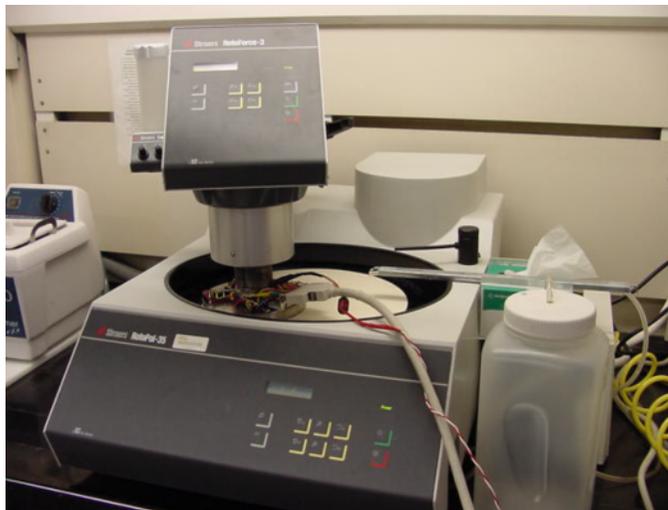
Bench top polisher
Struers. Photo by Rob Hight
Georgia Tech.

Polishing Pads

The most commonly used pad, IC-1000™, (Rohm and Haas) is a closed cell polyurethane foam with a mean void diameter of about 30 microns. Voids occupy about 35% of the volume and are not interconnected except at the surface.

The pad is shown here next to a scaled drawing of a 100 μm wide, 2 μm deep trench. The pad surface roughness is large compared with typical wafer features.
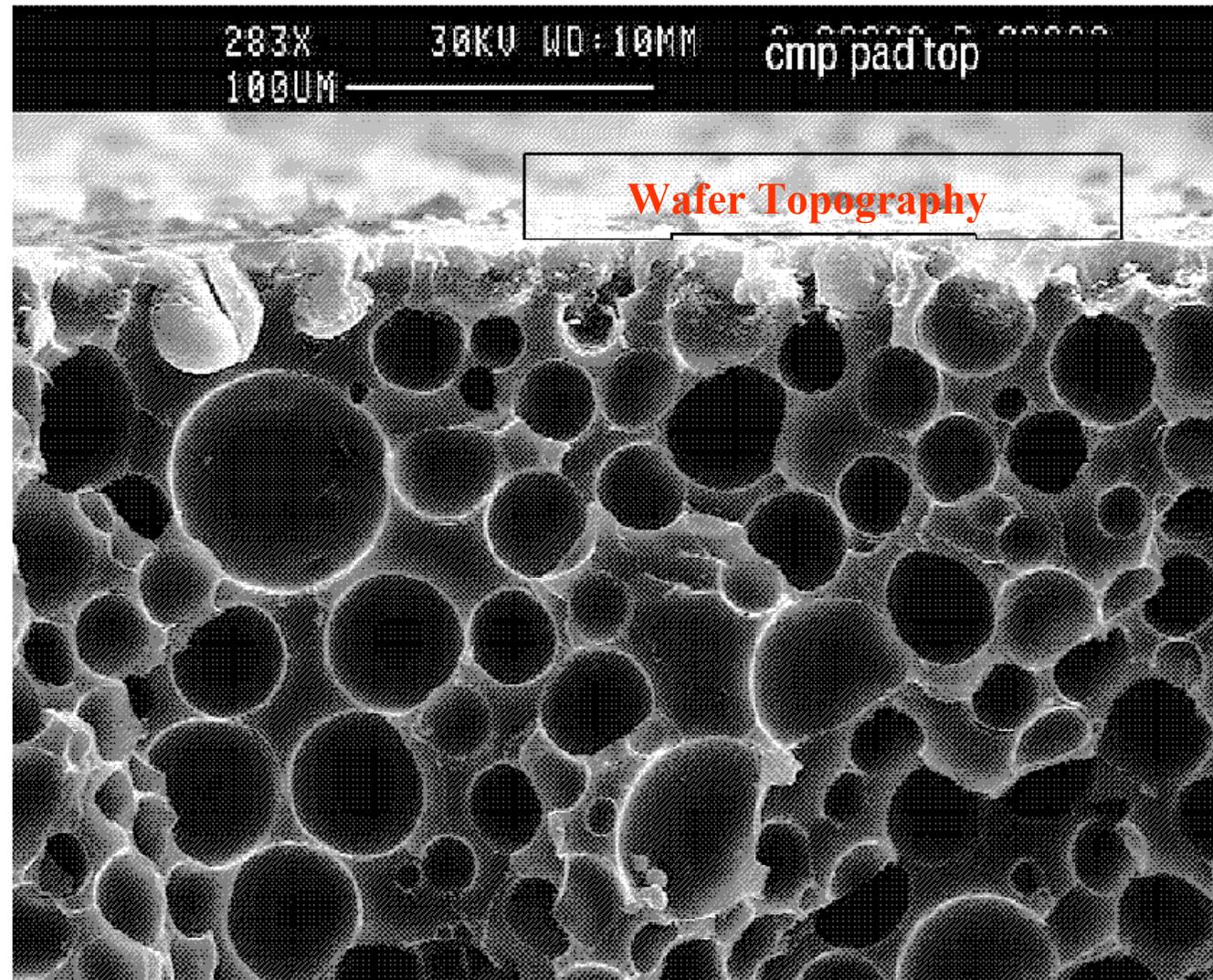
Letitia Molina, Motorola

Measured CMP Pad Properties

C.Elmufdi *et al.*, 2004 CAMP Symposium.

Material: IC1000™

Young's Modulus
$E = \sigma / \varepsilon$

σ, Engineering Stress, MPa

ε, Engineering Strain, %
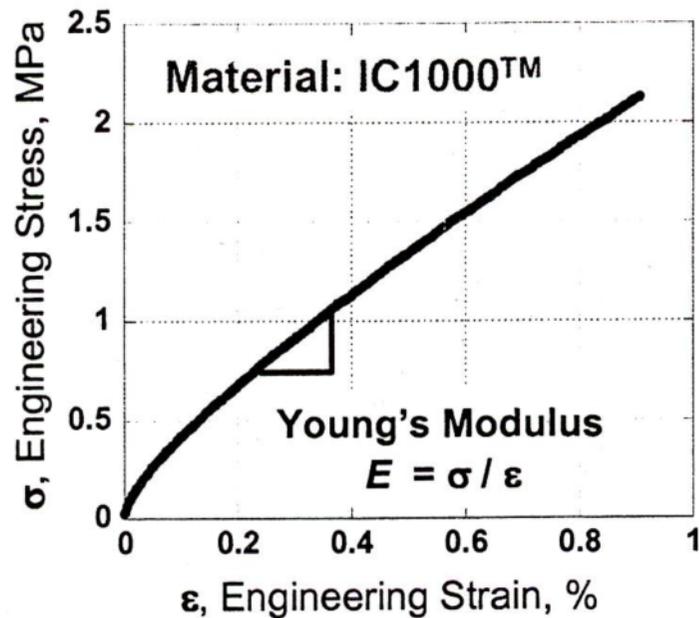
Material	Young's Modulus, E (MPa)
IC1000	285 ± 5
PSA	765 ± 45
SUBA IV (x direction)	80 ± 8
SUBA IV (y direction)	232 ± 20
Ungrooved IC1000 Stack (50 mil)	230 ± 10

Polishing pads are soft compared with most of the materials they polish.

Copper: 110 GPa   Silicon Dioxide: 43-77 GPa

The pad elastic modulus generally decreases with increasing temperature and water content. A wide range is possible: ~100-550 MPa.

Polishing Pad Surfaces

The pad surface is not static, but evolves under conditioning and abrasive wear.

Freshly conditioned

After polishing without conditioning

Kojima and
Nishiguchi,
2003 CMP-
MIC.

Scott Lawing,
Rohm and Haas
ECS 2003
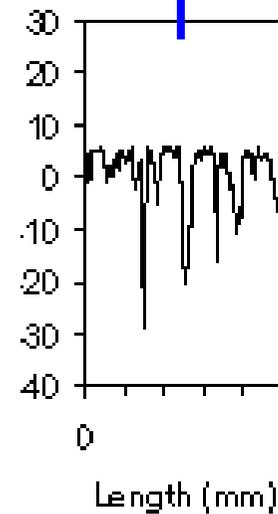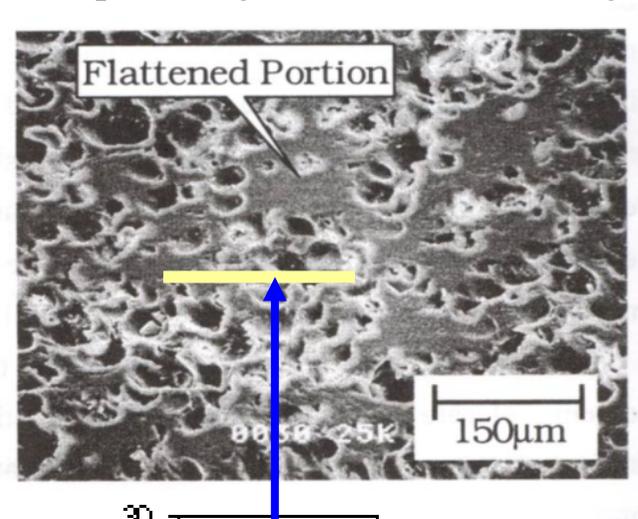
This shows that
there is pad/wafer
contact. The wear
rate varies with
the abrasive type.
Spherical particles
produce less wear,
irregular particles
more wear.

Slurry Particles

Slurry particles are very much smaller than pad asperities. Typical mean diameters for spherical colloidal particles range from a few tens to a few hundreds of nanometers. Solid loadings vary from ~0.3% to ~30% by weight. Slurry viscosity is similar to water.

We'll assume spherical colloidal particles
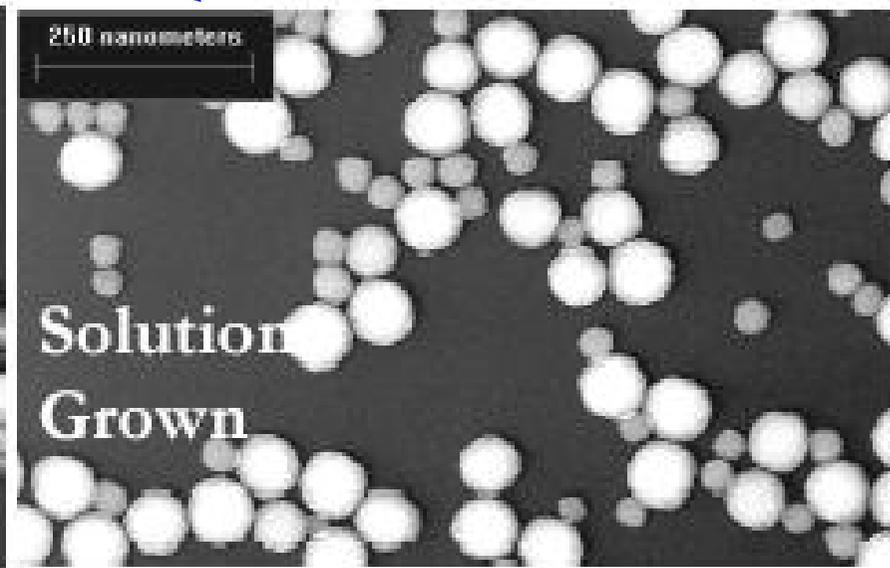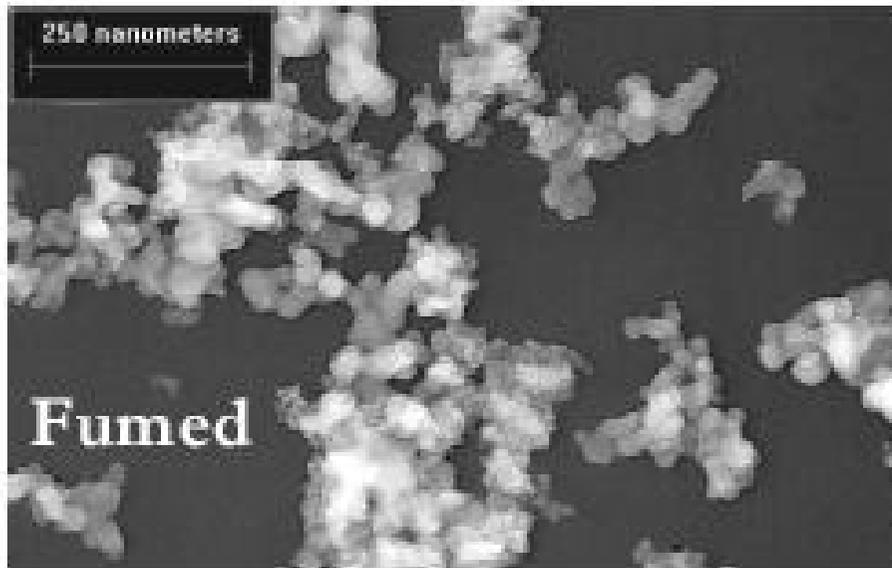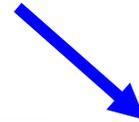
S. Lawing, ECS 2003

Polishing Mechanisms (SiO$_2$)

Chemical reaction/softening and mechanical removal.

Pressure p

Wafer (held upside down by carrier)

Chemically-softened layer with surface charge.

Reactive fluid and charged slurry particles
(Particle size greatly exaggerated)

Polishing pad

Relative sliding velocity V
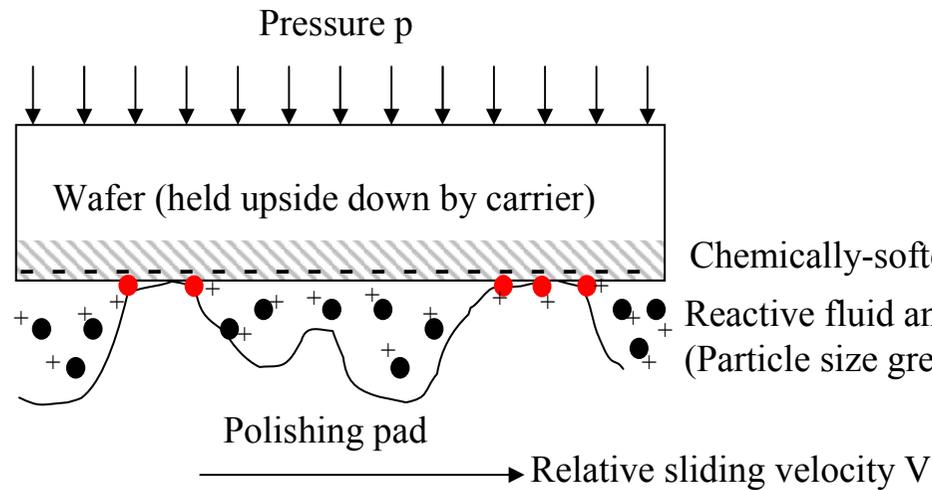
Hypothesized mechanism for SiO$_2$ removal by ceria. Most removed silica is found on the slurry particles and in colloidal suspension. (W. America, CAMP 2003).

Particle surface chemistry matters

- Si – O –
Ce –
HO

- Si – O –

- Si – O –

HO

- Si – O – ---------- Ce –
O

- Si – O –

HO
Ce –
O

Condensation

- OH

HO
HO -- Si – O – Ce -
HO

HO
HO -- Si – O -- Ce –
HO

HO
HO -- Si – O – Ce -

HO

Removal

+ HOH

ARACA
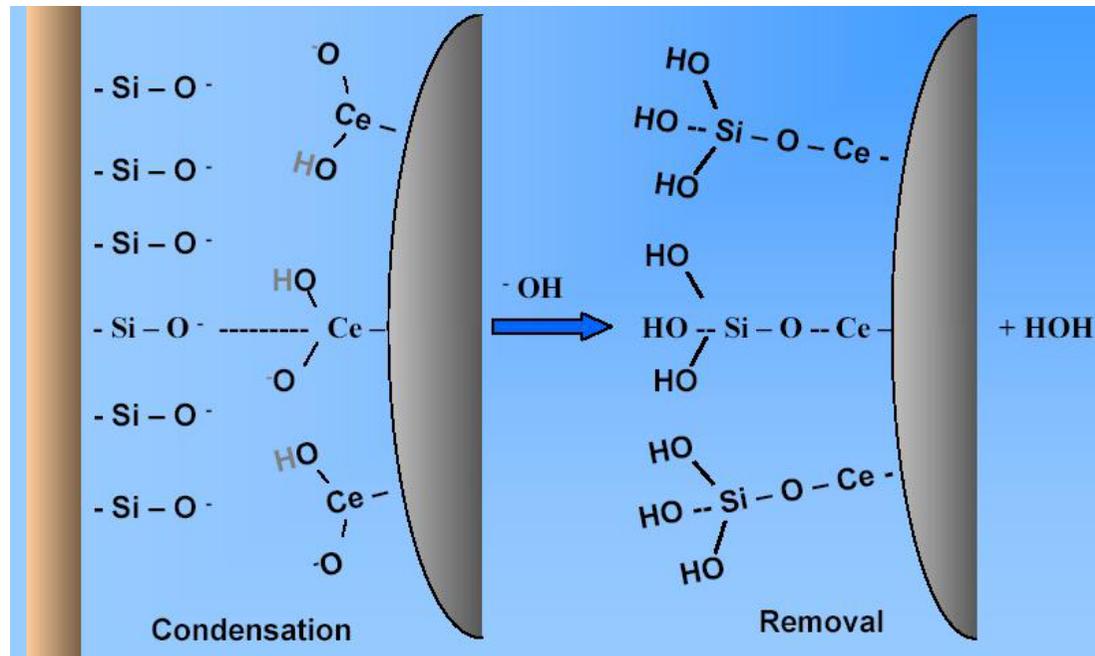
Summary of Scales and Numerical Values

Wafer $E \approx 1$ GPa

Nominal pressure p=7 - 49 kPa (1-7 PSI)
Relative sliding speed ~1 m/sec

Pad

$E \approx 100\text{-}500$ MPa

Slurry particles
tens-hundreds
of nm.

Pad asperities
and fluid
thickness –
tens of microns
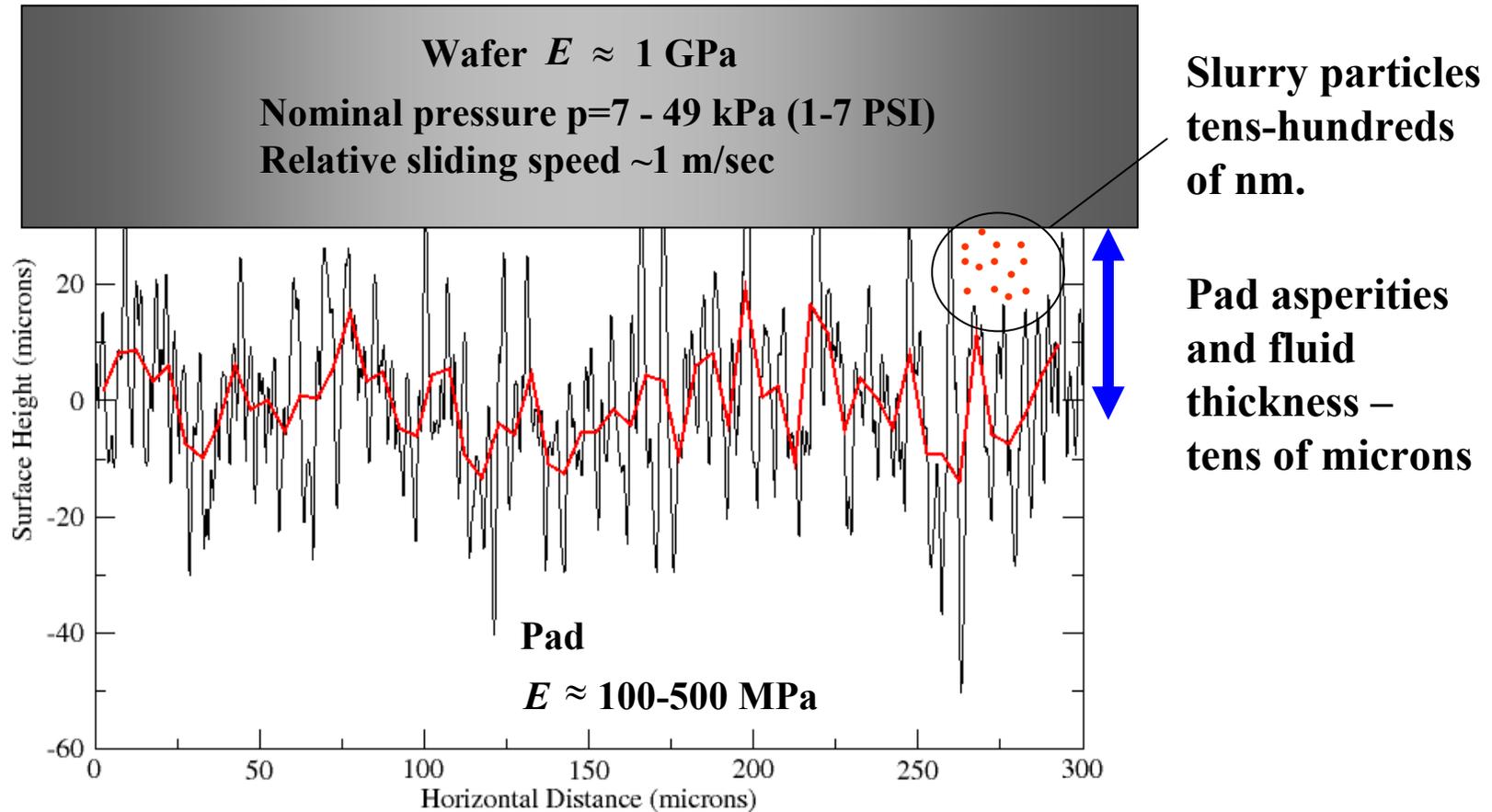
Elastohydrodynamic Lubrication (EHL)

Dry Contact

Hertzian Theory

o Undeformed asperity tips are spherical.

o Contact area is circular.

$$A = \pi a^2 = \pi R \delta$$

o Pressure is elliptic.

$$p = p_0 (1 - (r/a)^2)^{1/2}$$

$$p_0 = \frac{2E}{(1-\nu)\pi R^{1/2}} \delta^{1/2}$$
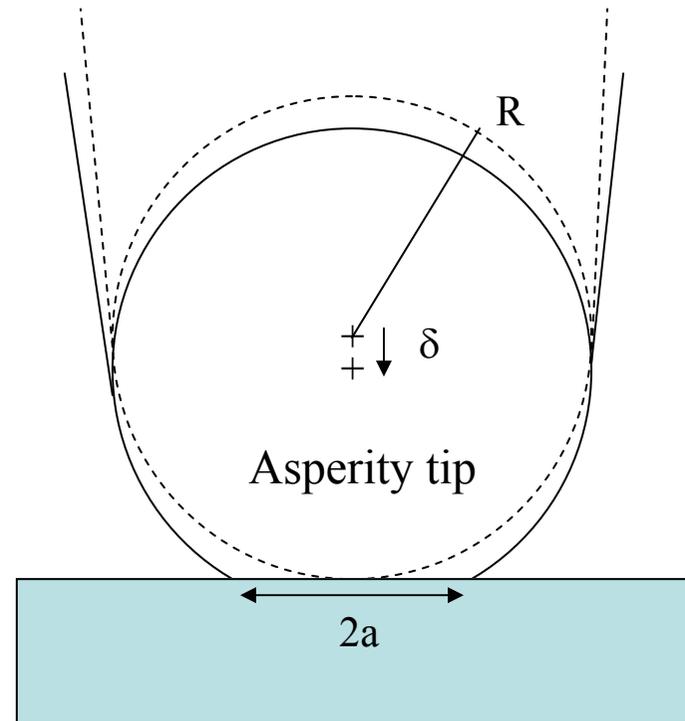
K.L. Johnson, *Contact Mechanics*

R

δ

Asperity tip

2a

ΛRACΛ

Lubricated Contact

EHL Theory

o A thin lubrication layer forms.

o Hydrodynamic pressures deform asperity tips.

o Positive hydrodynamic pressures in the lubrication layer support the load.

Wafer

V

Lubrication Layer

Asperity
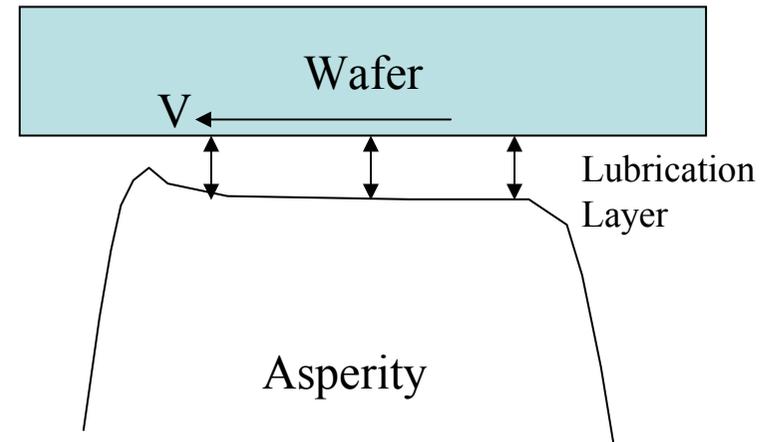
EHL Theories

Elastohydrodynamic lubrication has been studied for almost a century. Some early citations from Szeri, *Fluid Film Lubrication, Theory and Design,* Cambridge (1998) Ch. 8:

1916	H.M. Martin	Assumed rigid bodies. Predicted thinner lubrication layer than observed.
1936	W. Peppler	Allowed contacts to deform elastically.
1945	Gatcombe	Generalized to pressure-dependent viscosity, $\mu=\mu(p)$
1949	A.N. Grubin	First satisfactory solution accounting for elastic deformation and $\mu=\mu(p)$.

V ⟵

Reynolds equation

Elasticity theory

http://www.lsbu.ac.uk/water/explan2.html
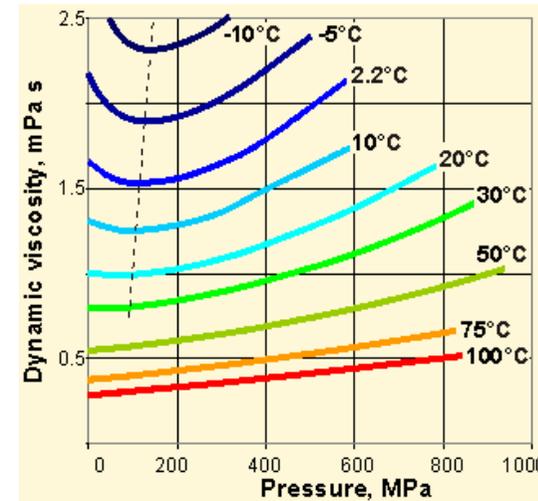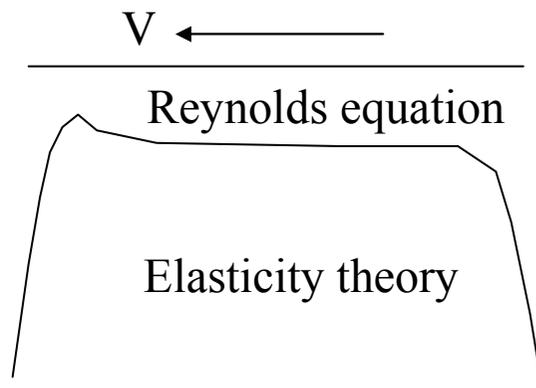
EHL Theory Example (Roller)

Fluid pressures are approximately the same as Hertzian pressures except for a pressure spike near the trailing edge. Disagreement becomes more pronounced at lower loads.

Fluid Pressure

Hertz theory

The lubrication layer is nearly uniform in thickness except for a constriction at the trailing edge that produces the pressure spike.

Asperity deformation

(a) $G = 5000.$

$W = 3 \times 10^{-4}.$
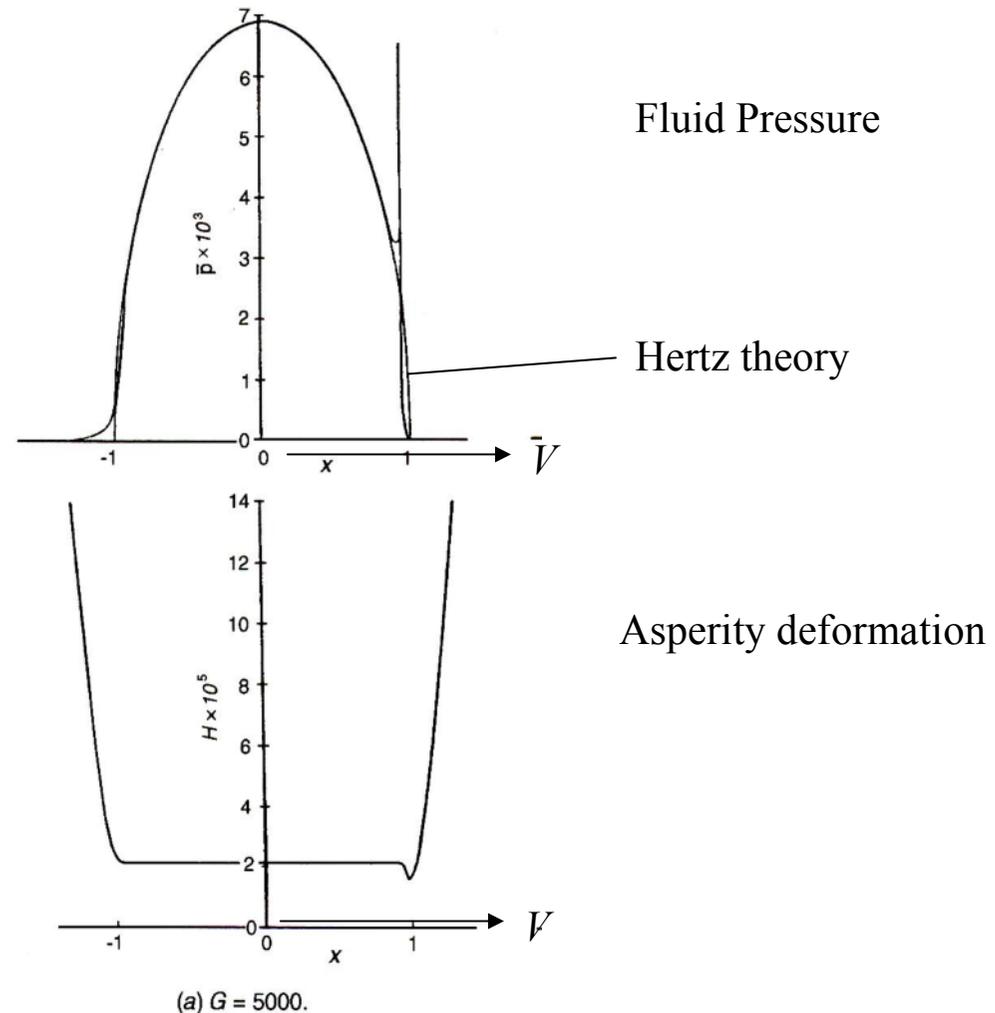
From Szeri, *Fluid Film Lubrication*, Cambridge University Press, 1998

EHL Compact Formulas

Simple formulas are often available for estimating the average lubrication layer thickness. Some fitting to more complex solutions is involved.

h_{min} h_c

Pad Asperity
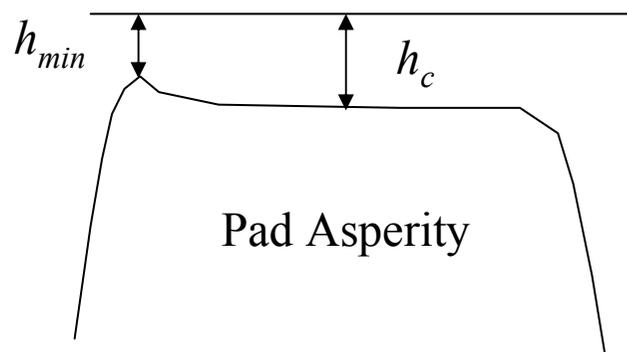
$$h_c = 1.5(\mu V)^{0.64} R^{0.8} E^{-0.42} p_{avg}^{-0.22}$$

$$p_{avg} = p / N_c$$

$$N_c = \eta_s \int_d^\infty \phi_s(z)dz$$

η_s = summit area density
ϕ_s = summit height PDF.

$\eta_s = 2 \times 10^8 / m^2$
ϕ_s Gaussian with $\sigma = 6\mu m$
$R = 50\mu m$
$p = 1$ kPa
$V = 1$ m/sec
$\mu = 2.5 \times 10^{-3}$ Pa-sec

→ *$h_c = 29$ nm*

about the same as the mean diameter of some types of slurry particles.

Slurry Particles

Active Particles

Polish rates are generally low for slurries that do not contain particles. When particles are added, some are evidently trapped between the wafer and pad asperities and increase the removal rate by mechanical or chemical means. These are **active** particles. Experimental estimates of slurry residence time and utilization suggest that most particles never become active.

Inactive

Active

Some active particles also abrade the pad.
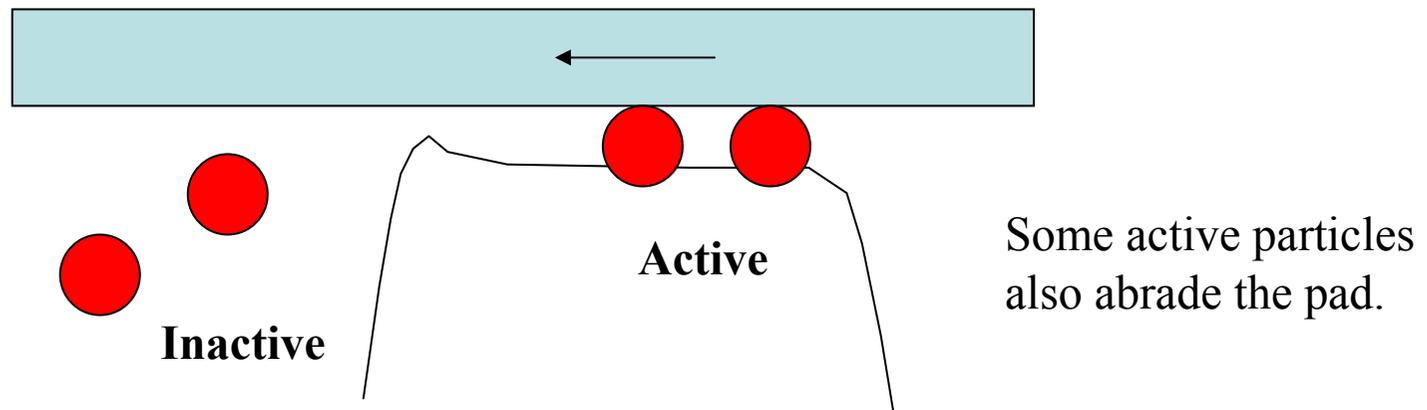
Removal Rate and Solids Loading

Removal rate increases with weight fraction for particles of a given size.

C. Zhou et al., STLE 2002
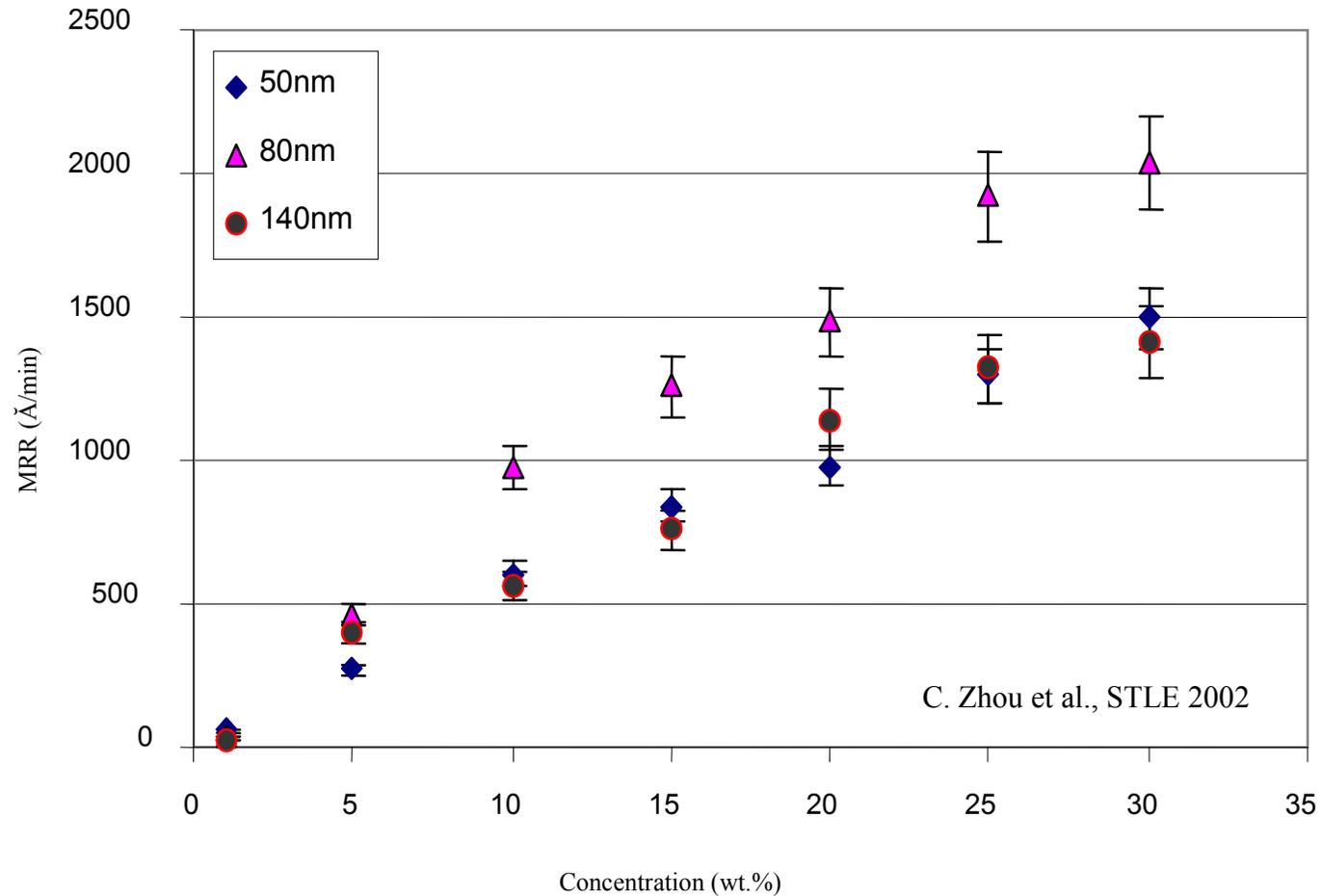
Removal Rate and Particle Size

At a fixed weight fraction, the removal rate has a peak at a size comparable to a possible lubrication layer thickness.
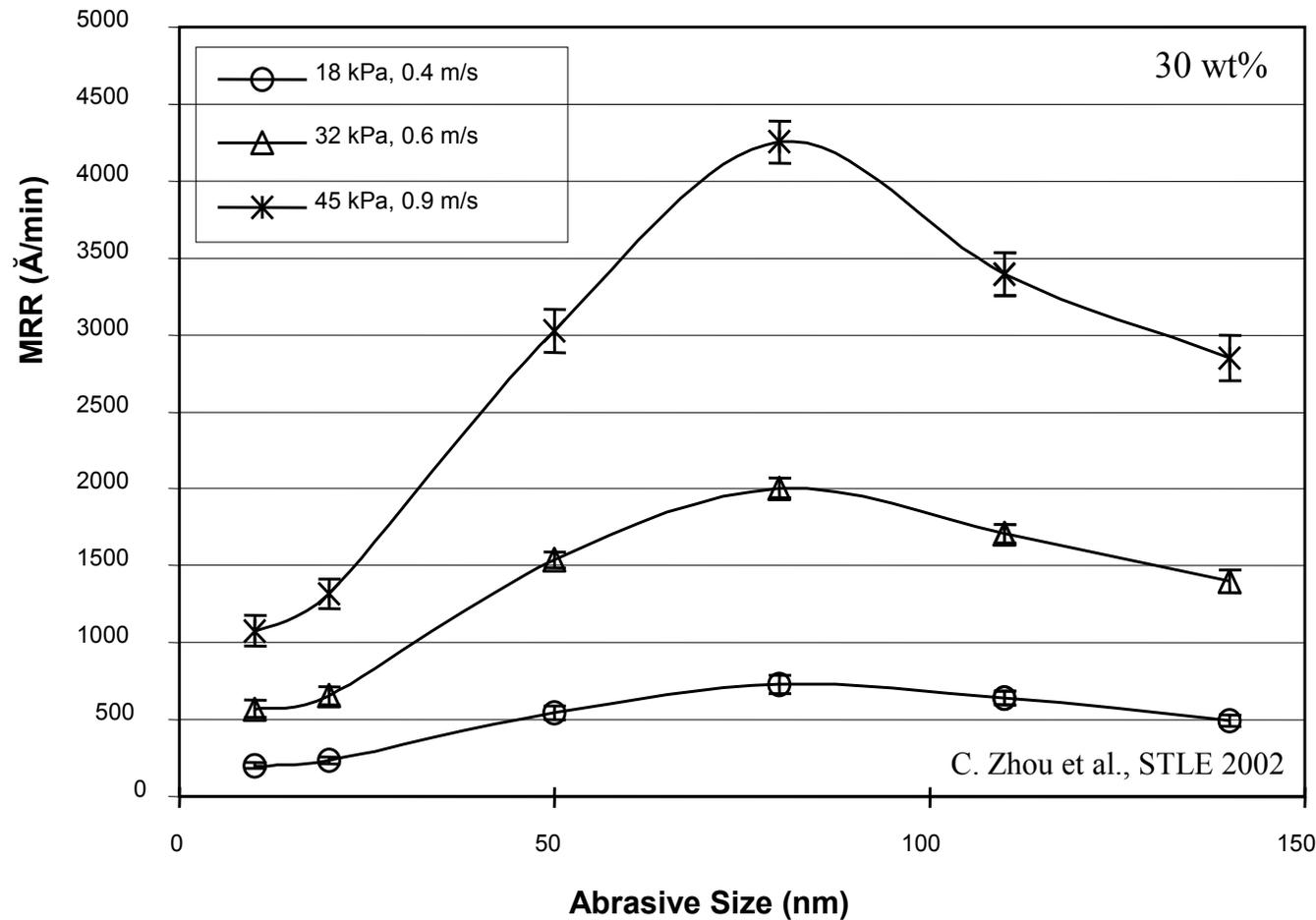
In this figure, the number of abrasive particles decreases as the size increases.

C. Zhou et al., STLE 2002

Questions

Which portion of the particle distribution becomes active?

If we start out with no particles in the lubrication layer, then how fast do they accumulate?

How much does the accumulation of a few particles affect the probability of capture of additional particles?

Slurry particle diameter

Small particle

not active

Medium

active

Large

active?

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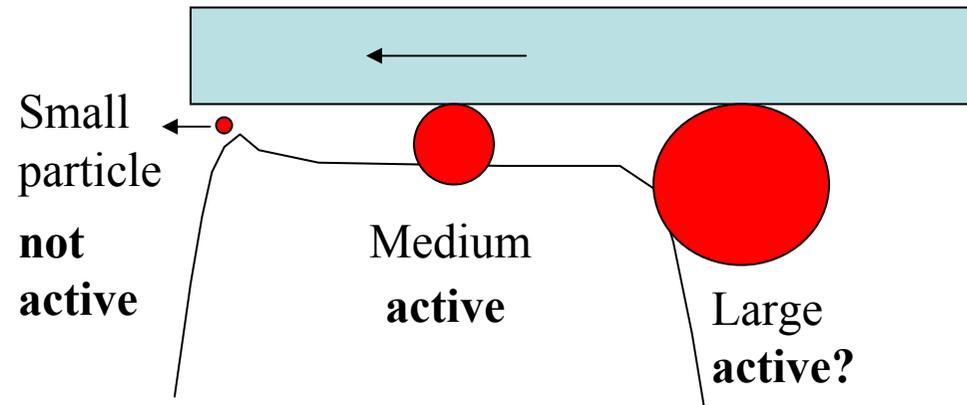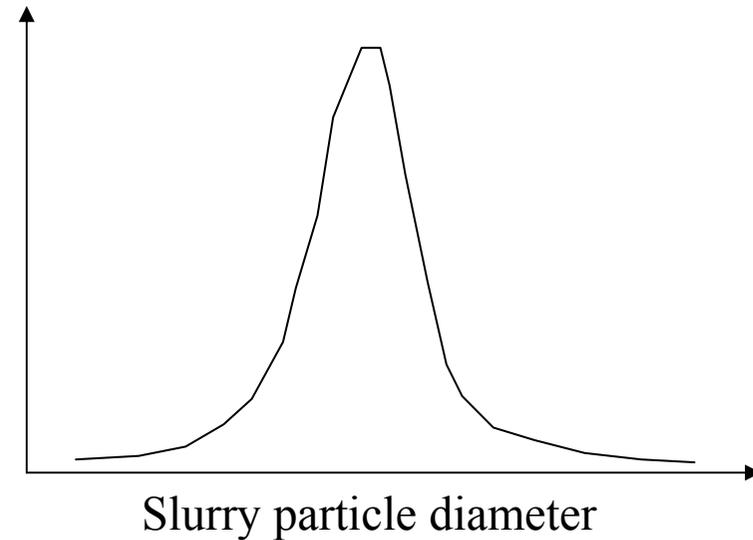
Questions

These are the main questions that I would like to address.

What happens to the thickness
and shape of the lubrication
layer as the solids loading
increases from zero to typical
upper weight fraction limits?

Are hydrodynamic pressures
the main determinant of the
layer geometry or is there
a point at which particle size
and loading are the main factors?

Can the compact models of
lubrication layer thickness
be generalized to include
slurry particles?

No solids

?

High solids loading

ARACA
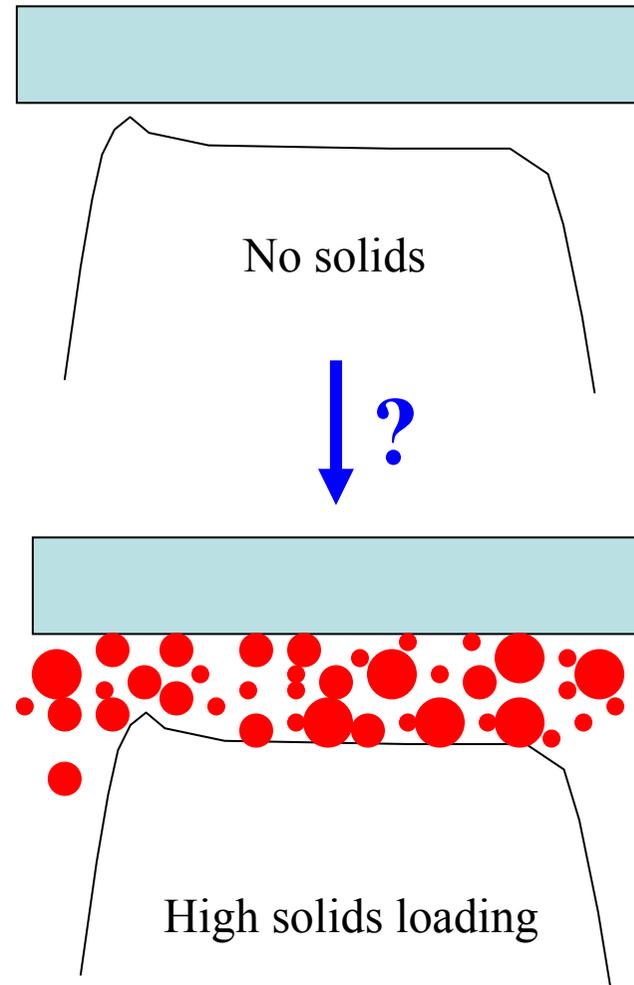
I have with me …

1. A 2D finite element Reynolds equation solver.
2. A 2D/3D linear elasticity solver.
3. Some literature.

Fluid pressures from the Reynolds solver